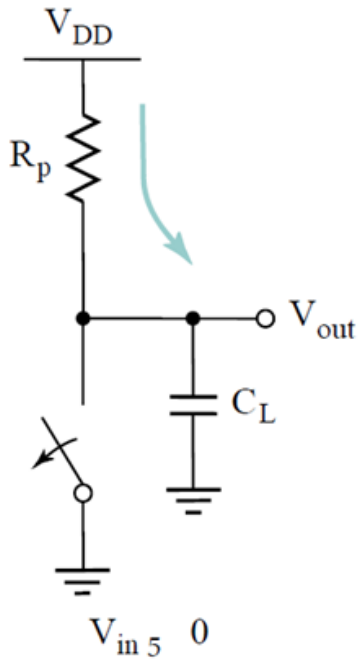


Design practical considerations in Integrated Circuits

CMOS propagation time

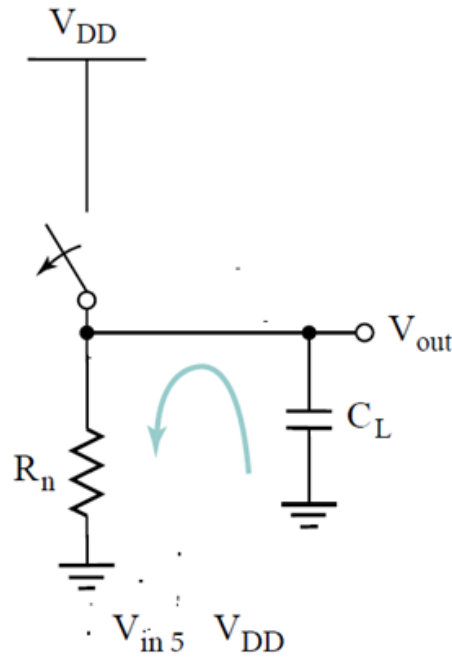


(a) Low-to-high

$$V_{out} = V_{DD}(1 - e^{-t/\tau})$$

$$t_P: V_{out}(50\%) = \frac{V_{DD}}{2} = V_{DD}(1 - e^{-t_P/\tau})$$

$$\frac{1}{2} = e^{-t_P/\tau} \Rightarrow t_{PP} = \ln 2 \cdot \tau = \ln 2 \cdot R_P \cdot C_L$$



(b) High-to-low

$$V_{out} = V_{DD}e^{-t/\tau}$$

**Symmetric propagation times,
by desing iiii**

$$t_{PN} = t_{PP} \Rightarrow \tau_P = \tau_P \Rightarrow R_P = R_N = R_{eq}$$

$$t_{p_{HL}} = t_{p_{LH}} = \ln(2) \cdot R_{eq} \cdot C_L$$

LOAD

$$R_{eq} = R_s \frac{L}{W}$$

$L_n = L_p$
The smallest possible

Constant for a material

W can be chosen

CMOS propagation time (Load)

➤ Parasitic Capacitance

❖ Transistor gate capacitance(C_g):

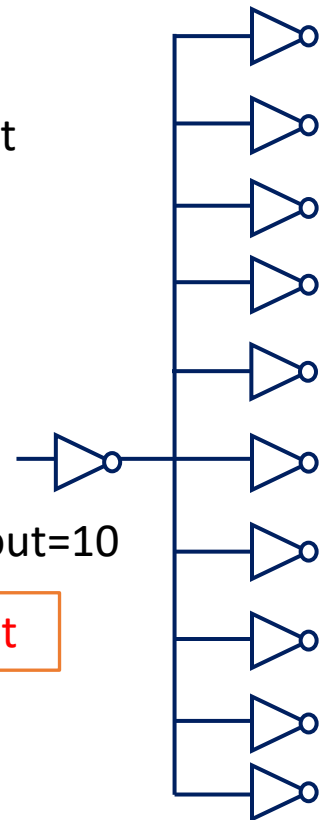
$$C_g = C_{ox} * W * L$$

Capacitance per area unit

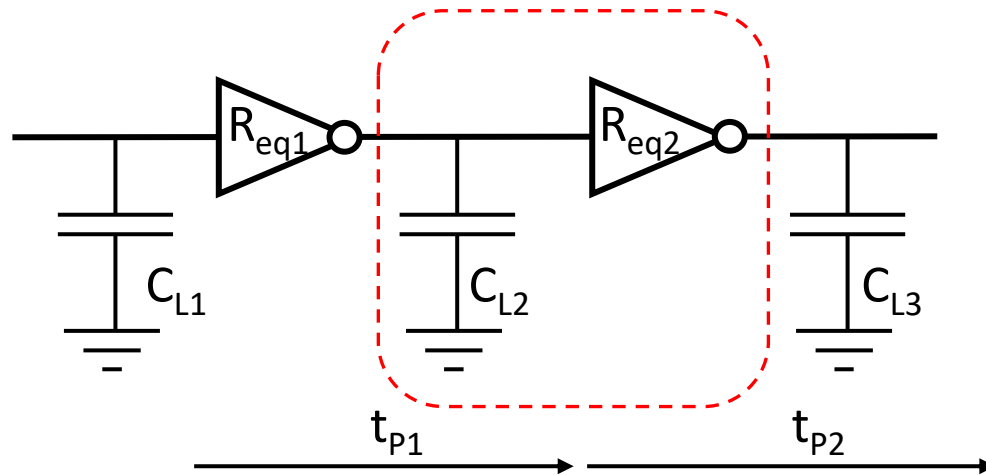
❖ Interconexión capacitance:

- Increase with Length
- More important with small technologies

Fan-out is the number of **load gates** connected to the **output**



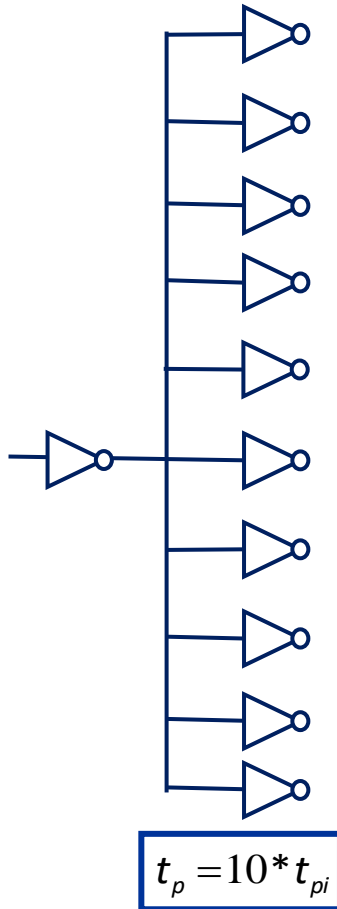
CMOS propagation time (Load)



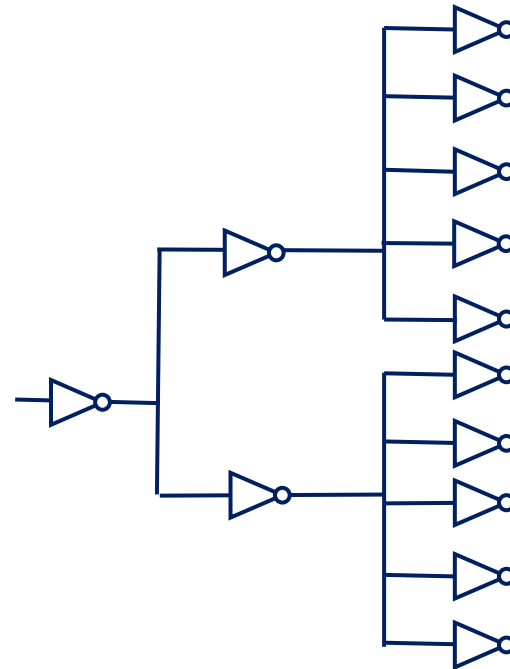
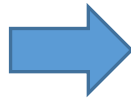
- ❑ R_p, R_n (R_{eq}) are decreased by making transistors BIGGER
- ❑ C_L is decreased by making transistors SMALLER

CMOS propagation time (Load)

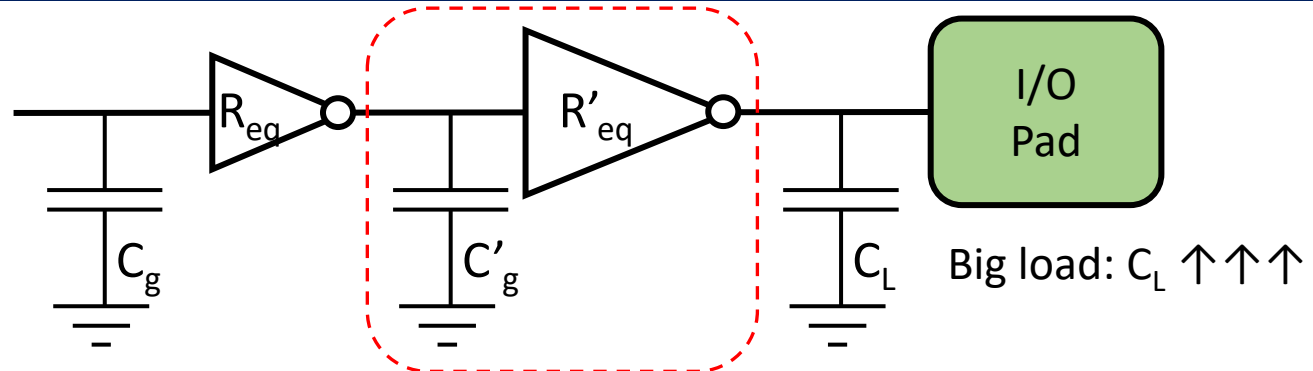
- Delay due to high fanout



$t_{pi} = t_p$ of the
minimum size
inverter



CMOS propagation time (Load)



- Delay reduction in propagation time (t_p)

$$t_p = \ln(2) \cdot R_{eq} \cdot C_L$$

$$R_{eq} = R_s \frac{L}{W}$$

$$C_g = C_{ox} \cdot L \cdot W$$

- ❖ Increase channel width ($W \rightarrow W'$):

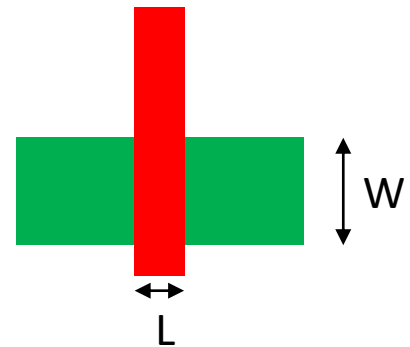
$$W' = \Theta \cdot W$$

$$\Theta > 1$$

$$W' \uparrow$$

$$R'_{eq} \downarrow$$

$$C'_g \uparrow$$



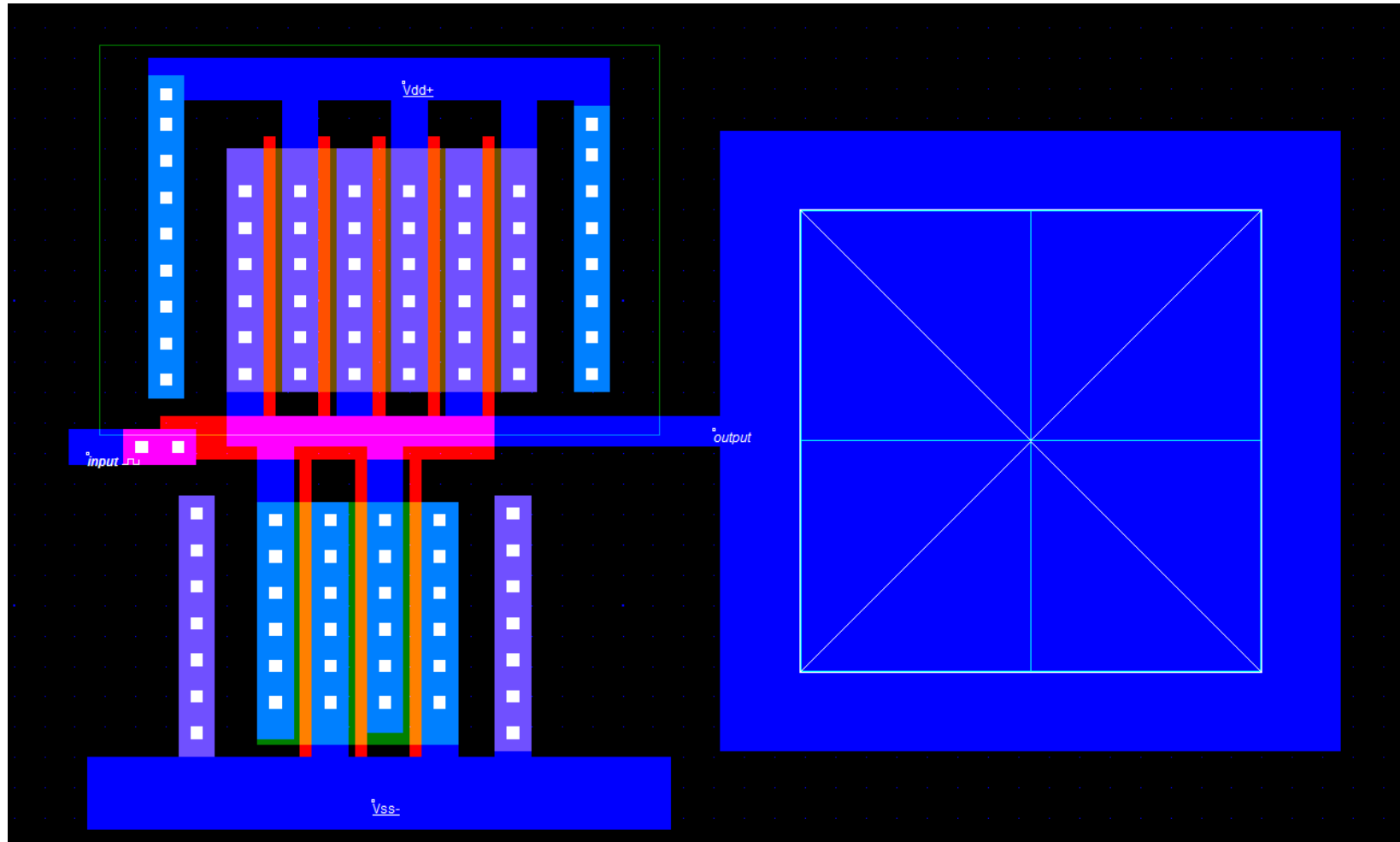
Bad: Area penalty

Good: Delay reduction

Move the delay to previous gate.
Good only if $C_L \gg C_g$

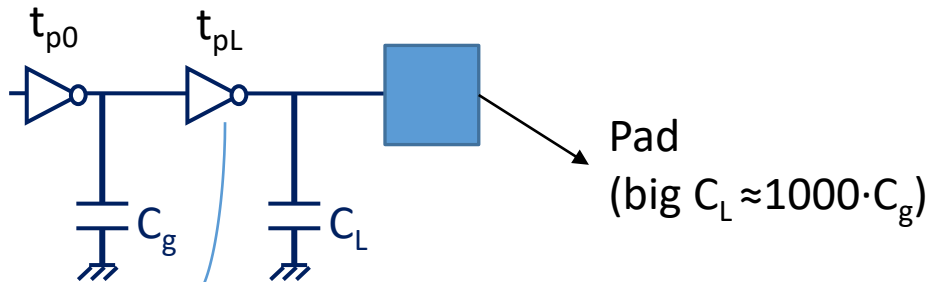
Tiempo de propagación CMOS

Indivisible Load: output pad



CMOS propagation time (Load)

➤ Indivisible Load (C_L)



$$t_p = t_{pi} + 1000 \cdot t_{pi} = 1001 \cdot t_{pi}$$

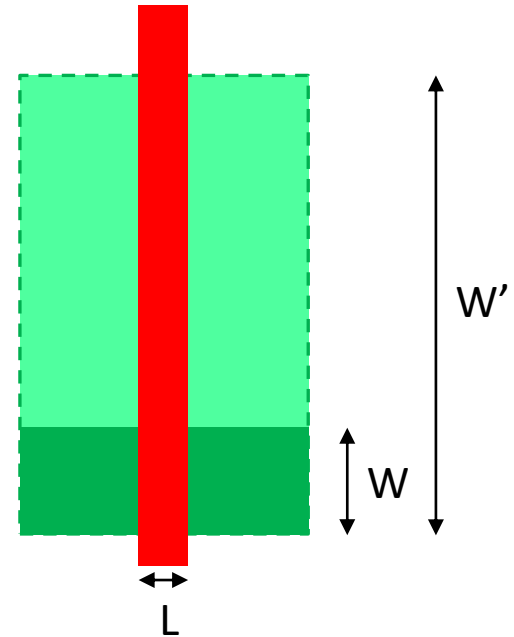
Bigger transistors: 50 times bigger

$$\Theta = 50 \Rightarrow W' = 50 \cdot W \Rightarrow R_{eq}' = R_{eq}/50 \Rightarrow t_{pL}' = t_{pL}/50 = 1000 \cdot t_{pi}/50 = 20 \cdot t_{pi}$$

But:

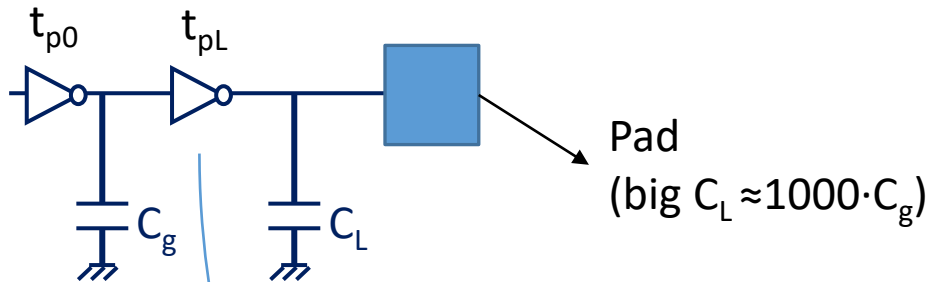
$$t_{p0}' = \Theta \cdot t_{p0} = 50 \cdot t_{pi}$$

70 · t_{pi} instead
of 1001 · t_{pi}

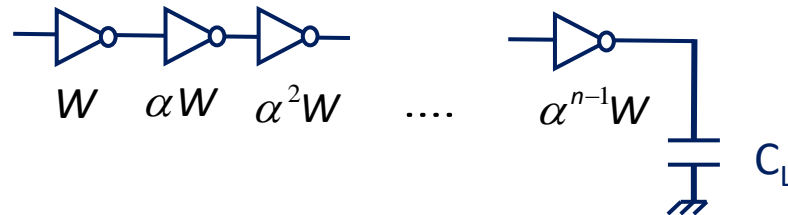


CMOS propagation time (Load)

➤ Indivisible Load (C_L)

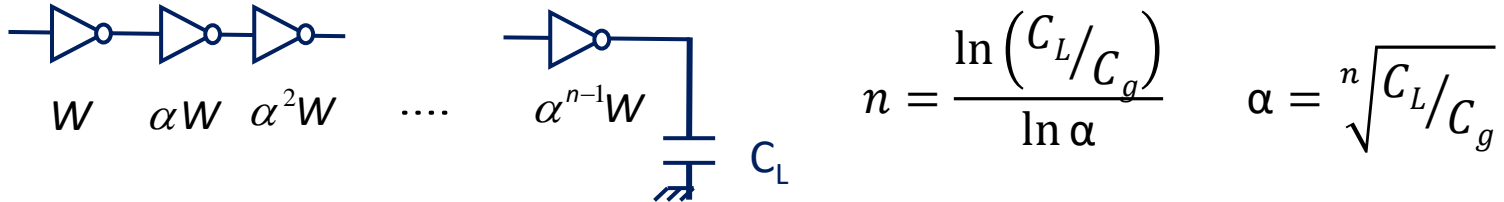


Best solution: several inverter stages with increasing size



CMOS propagation time (Load)

Best solution: several stages (n) with increasing sizes (α) so that: $C_L = \alpha^n C_g$

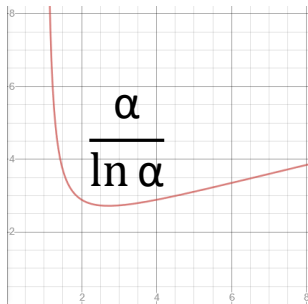


1 stage delay:

$$t_{pk} = \ln(2) \cdot \frac{R_{eq}}{\alpha^k} \cdot \alpha^{k+1} C_g = \alpha \cdot \ln(2) \cdot R_{eq} \cdot C_g = \alpha \cdot t_{pi}$$

Total delay (n stages):

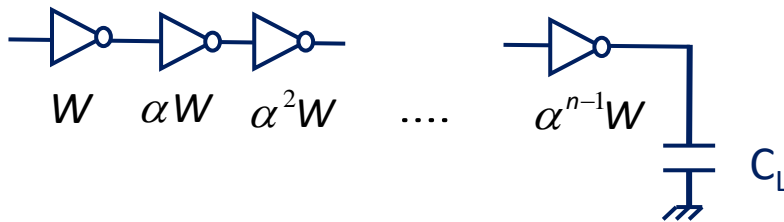
$$t_p = n \cdot \alpha \cdot t_{pi} = \frac{\ln(C_L/C_g)}{\ln \alpha} \cdot \alpha \cdot t_{pi} = t_{pi} \cdot \ln(C_L/C_g) \cdot \frac{\alpha}{\ln \alpha}$$



Minimum: $\frac{dt_p}{d\alpha} = Cte \cdot \frac{\ln \alpha - 1}{(\ln \alpha)^2} = 0 \Rightarrow \alpha = e \Rightarrow n = \ln(C_L/C_g)$

CMOS propagation time (Load)

Best solution:



Example: $C_L = 1000 C_g$

$$n = \ln \frac{C_L}{C_g} = \ln 1000 = 6,9 \approx 7$$

Recalculate α :

$$\alpha = \sqrt[7]{1000} = 2,68$$

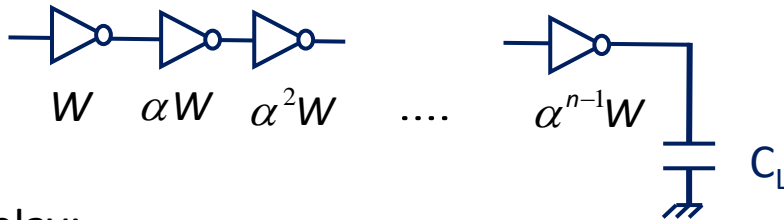
$$t_{pi} = \ln(2) \cdot R_{eq} \cdot C_g$$

$$A_0 = L \cdot W$$

Stage	1	2	3	4	5	6	7
Size	W	αW	$\alpha^2 W$	$\alpha^3 W$	$\alpha^4 W$	$\alpha^5 W$	$\alpha^6 W$
R	R_{eq}	R_{eq}/α	R_{eq}/α^2	R_{eq}/α^3	R_{eq}/α^4	R_{eq}/α^5	R_{eq}/α^6
C	αC_g	$\alpha^2 C_g$	$\alpha^3 C_g$	$\alpha^4 C_g$	$\alpha^5 C_g$	$\alpha^6 C_g$	$C_L = \alpha^7 C_g$
R·C	$\alpha R_{eq} C_g$	$\alpha R_{eq} C_g$	$\alpha R_{eq} C_g$	$\alpha R_{eq} C_g$	$\alpha R_{eq} C_g$	$\alpha R_{eq} C_g$	$\alpha R_{eq} C_g$
Area	A_0	αA_0	$\alpha^2 A_0$	$\alpha^3 A_0$	$\alpha^4 A_0$	$\alpha^5 A_0$	$\alpha^6 A_0$

CMOS propagation time (Load)

Best solution:



Example: $C_L = 1000 C_g$

$$n = \ln \frac{C_L}{C_g} = \ln 1000 = 6,9 \approx 7$$

$$\alpha = \sqrt[7]{1000} = 2,68$$

Total delay:

$$t_p = \sum_{k=1}^n t_i = \sum_{k=0}^n (\ln(2) \cdot \alpha R_{eq} C_g) = \ln(2) \cdot R_{eq} C_g \cdot \alpha \cdot n = \alpha \cdot n \cdot t_{pi}$$

$$t_p = \alpha \cdot n \cdot t_{pi} = 2,68 \cdot 7 \cdot t_{pi} = \mathbf{18.7} \cdot t_{pi}$$

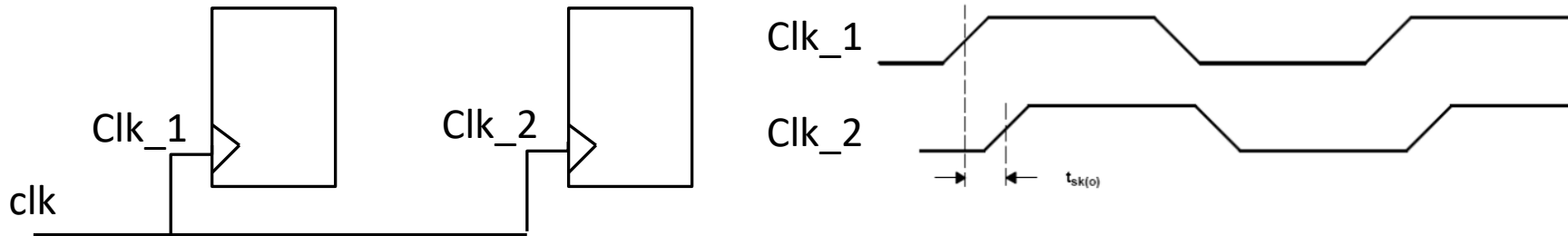
Total area:

$$A = \sum_{k=0}^{n-1} \alpha^k A_o = \frac{\alpha^n - 1}{\alpha - 1} A_o$$

$$A = \frac{\alpha^n - 1}{\alpha - 1} A_o = \frac{2.68^7 - 1}{2.68 - 1} A_o = \mathbf{590} \cdot A_o$$

Clock distribution

- ❖ Very high fanout
- ❖ Clock-skew: difference time clock arrival between flip-flops



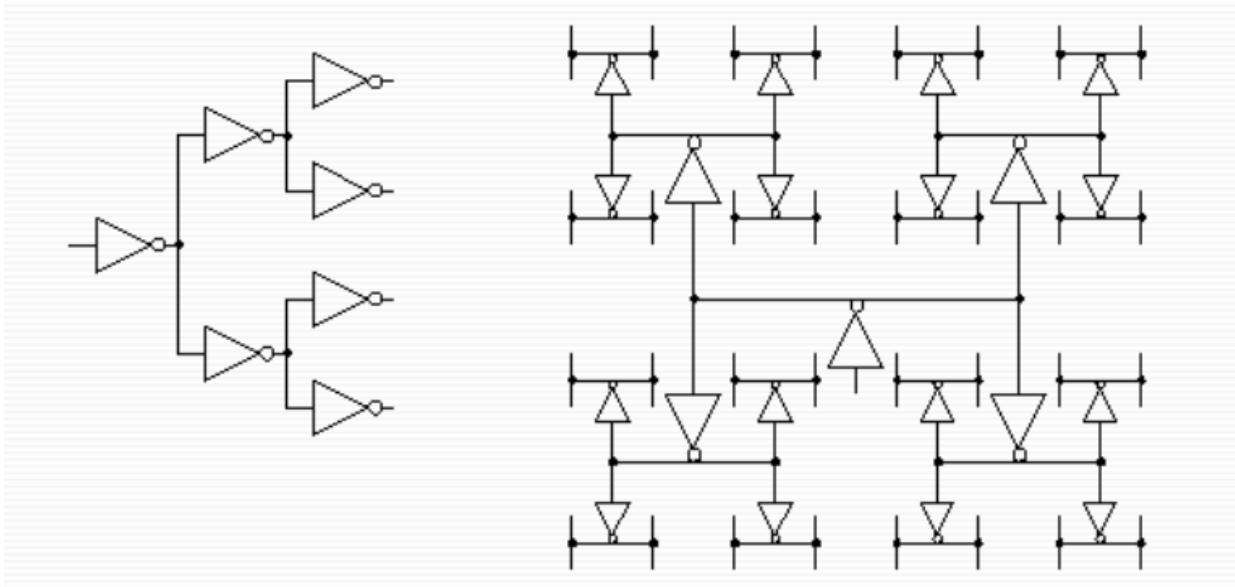
Solutions:

- Routing the clock in the opposite sense to combinational logic.
- Appropriate clock network: clock tree
- Clock buffers.
- Increase the width of the wires to reduce the resistance

Clock distribution

Solutions:

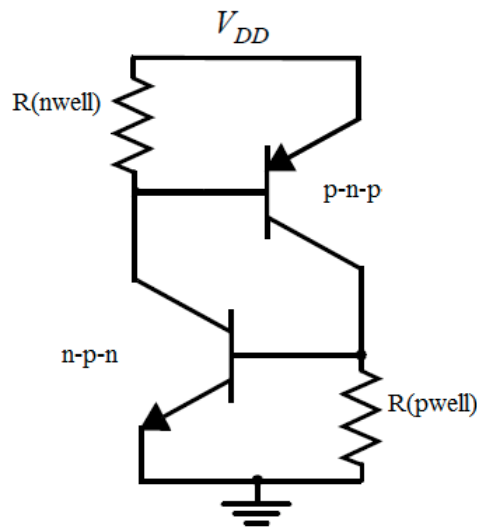
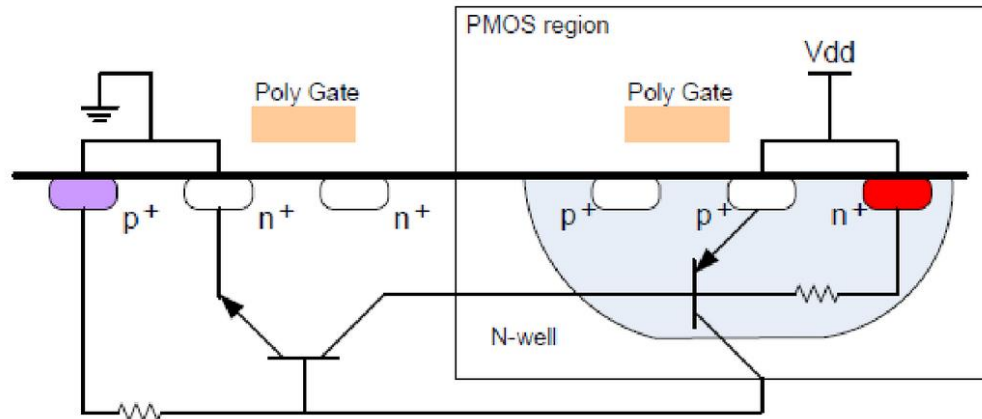
- Appropriate clock network: clock tree
- Clock buffers.



❖ Similar problems appear in the reset signal =>
solution: big buffer and increase the width of the wires.

Latch-up

A *latch-up* is a type of short circuit which can occur in an integrated circuit (IC).



Normal conditions

pnp no conducting



No Voltage through $R(nwell)$



pnp off



No Voltage through $R(pwell)$



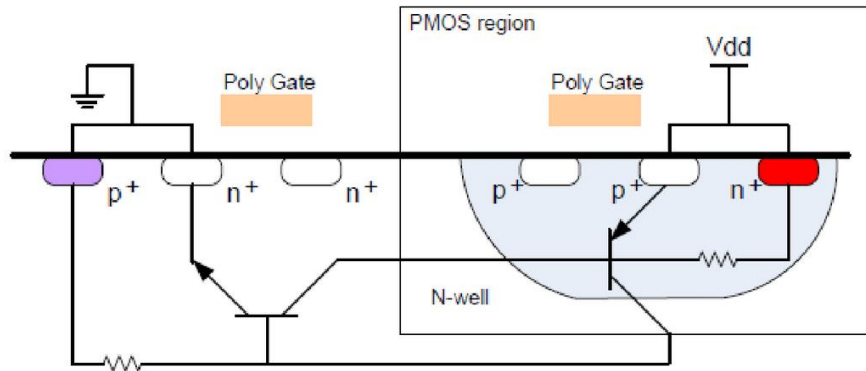
pnp off

Overpowering, radiation, particles

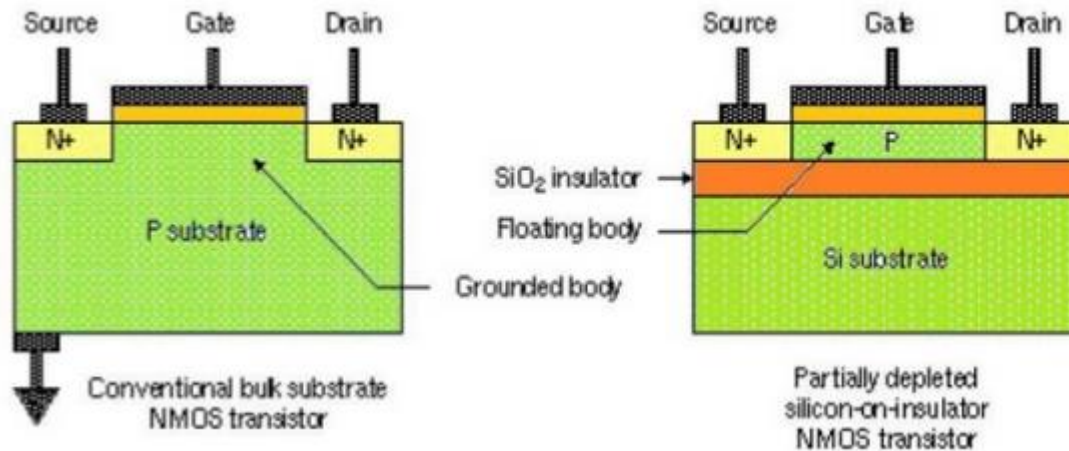
During a latch-up when one of the transistors is conducting, the other one begins conducting too. They both keep each other in saturation for as long as the structure is forward-biased and some current flows through it.

Latch-up

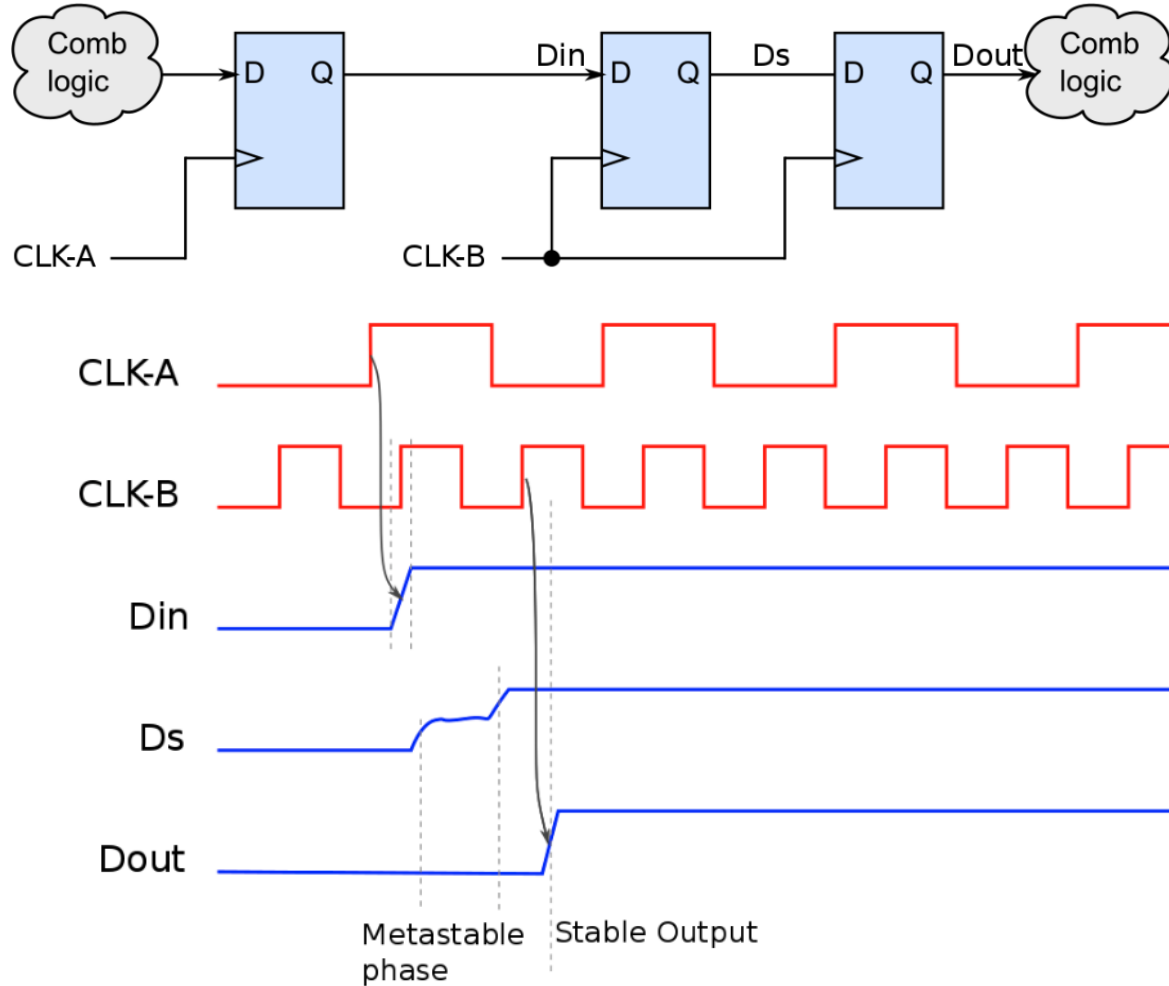
A *latch-up* is a type of short circuit which can occur in an integrated circuit (IC).



Solution: **Silicon on insulator (SOI)** technology.



Metastability



Whenever there are setup and hold time violations in any flip-flop, it enters a state where its output is unpredictable: this state is known as metastable state (quasi stable state); at the end of metastable state, the flip-flop settles down to either '1' or '0'.